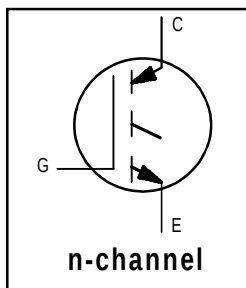


Features

- Short Circuit Rated UltraFast: Optimized for high operating frequencies >5.0 kHz , and Short Circuit Rated to 10μs @ 125°C, $V_{GE} = 15V$
- Generation 4 IGBT design provides higher efficiency than Generation 3
- Industry standard TO-252AA package



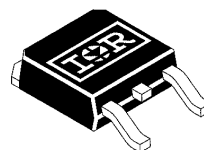
$$V_{CES} = 600V$$

$$V_{CE(on)} \text{ typ.} = 2.39V$$

$$@V_{GE} = 15V, I_C = 5.0A$$

Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions



D-PAK
TO-252AA

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	9.0	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	5.0	
I_{CM}	Pulsed Collector Current ①	18	
I_{LM}	Clamped Inductive Load Current ②	18	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	34	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	38	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	15	
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	3.3	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	—	50	
Wt	Weight	0.3 (0.01)	—	g (oz)

* When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994
www.irf.com

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.58	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.39	2.62	V	$I_C = 5.0A, V_{GE} = 15V$
		—	3.25	—		$I_C = 9.0A, V_{GE} = 15V$
		—	2.63	—		$I_C = 5.0A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	1.2	1.8	—	S	$V_{CE} = 50V, I_C = 5.0A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	19	29	nC	$I_C = 5.0A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	2.9	4.3		$V_{CC} = 400V, V_{GE} = 15V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	9.8	15		See Fig.8
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 5.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 100\Omega$
t_r	Rise Time	—	24	—		
$t_{d(off)}$	Turn-Off Delay Time	—	51	77		
t_f	Fall Time	—	190	290		
E_{on}	Turn-On Switching Loss	—	0.16	—	mJ	Energy losses include "tail" See Fig. 9,10,14
E_{off}	Turn-Off Switching Loss	—	0.10	—		
E_{ts}	Total Switching Loss	—	0.26	0.32		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 400V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 100\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$T_J = 150^\circ\text{C}$ $I_C = 5.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 100\Omega$
t_r	Rise Time	—	27	—		
$t_{d(off)}$	Turn-Off Delay Time	—	67	—		
t_f	Fall Time	—	350	—		
E_{ts}	Total Switching Loss	—	0.47	—	mJ	See Fig. 10,11,14
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	220	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$
C_{oes}	Output Capacitance	—	29	—		
C_{res}	Reverse Transfer Capacitance	—	7.5	—		

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = 10\mu H$, $R_G = 100\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

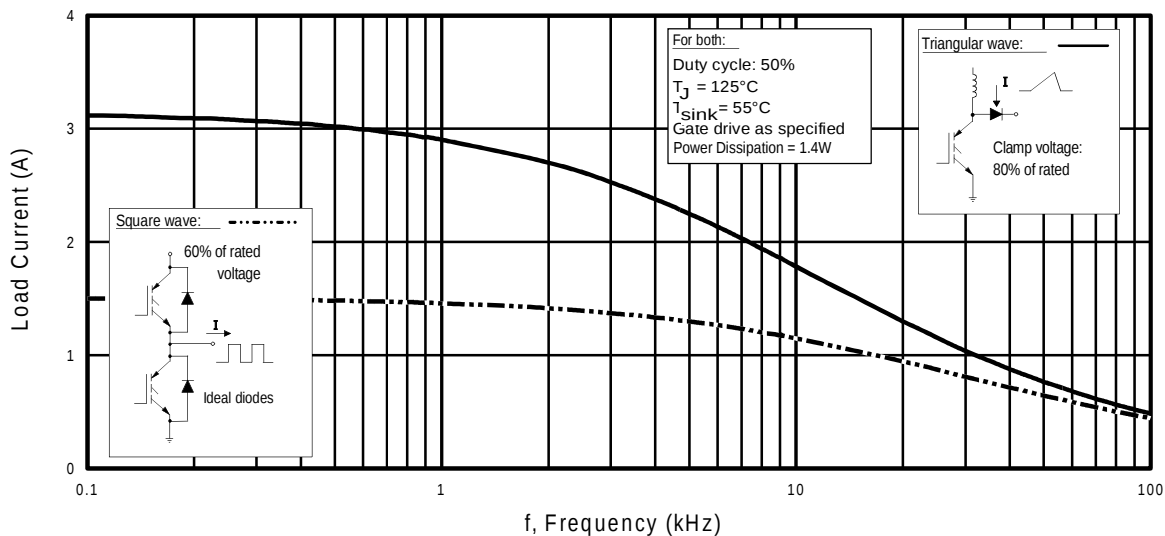


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

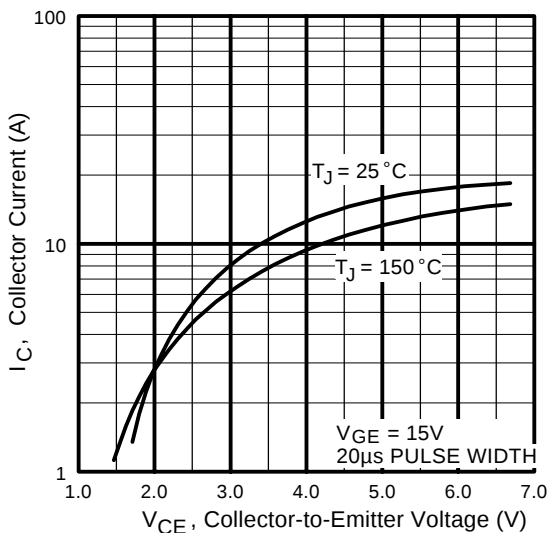


Fig. 2 - Typical Output Characteristics

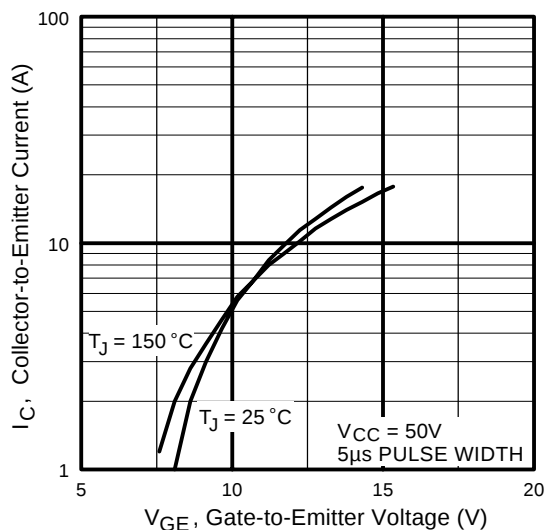


Fig. 3 - Typical Transfer Characteristics

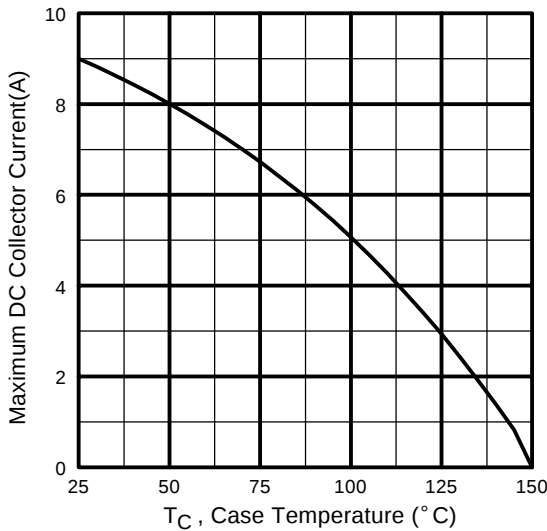


Fig. 4 - Maximum Collector Current vs. Case Temperature

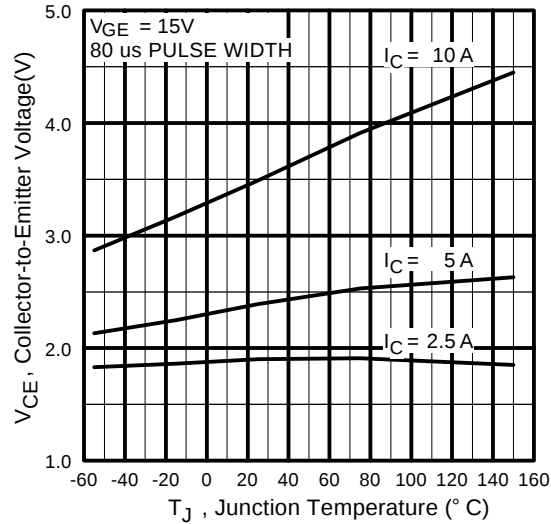


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

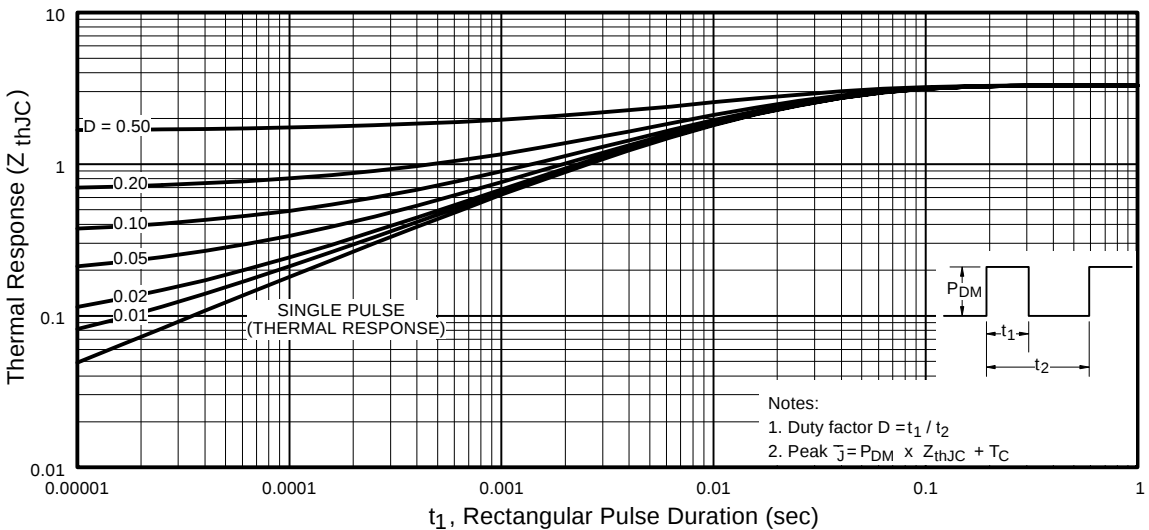
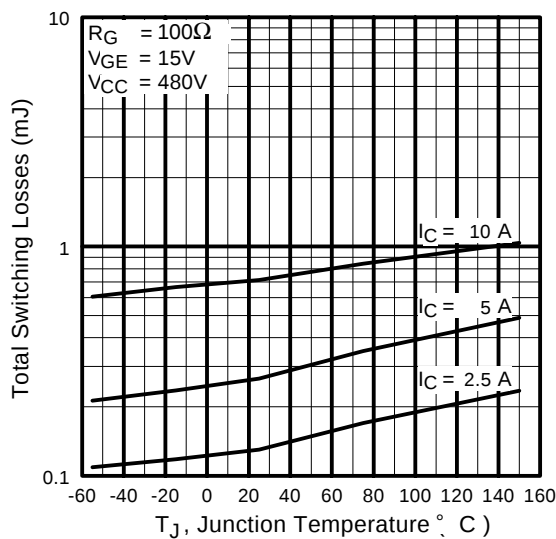
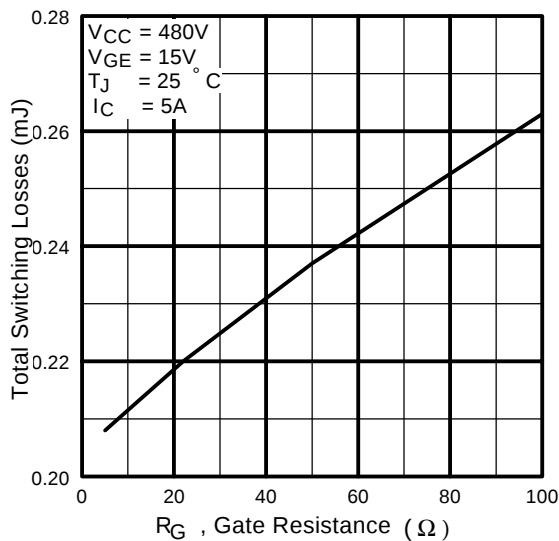
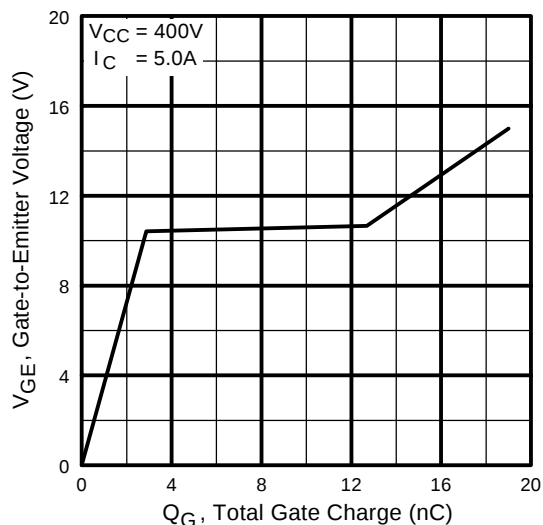
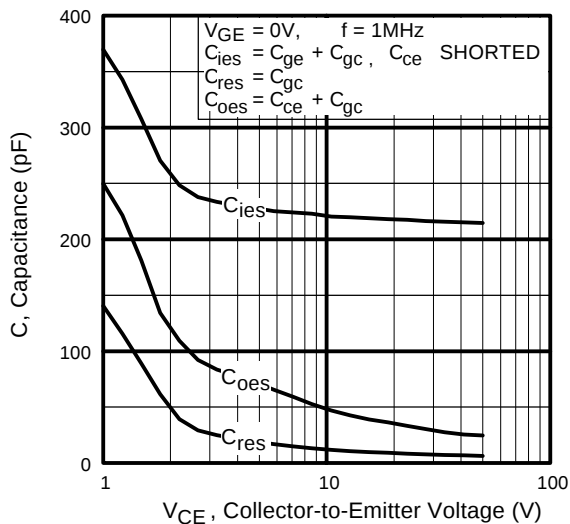


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



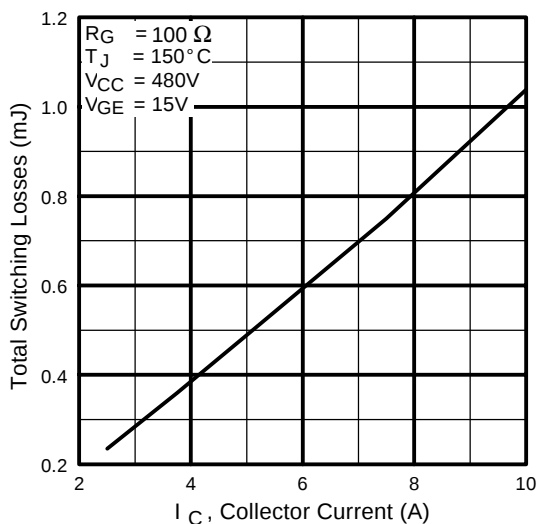


Fig. 11 - Typical Switching Losses vs. Collector Current

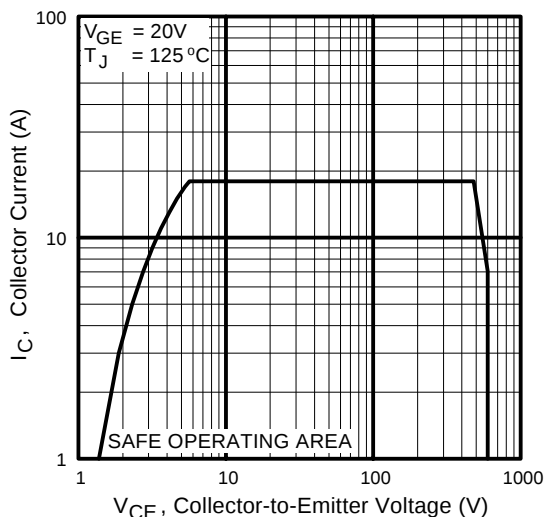


Fig. 12 - Turn-Off SOA

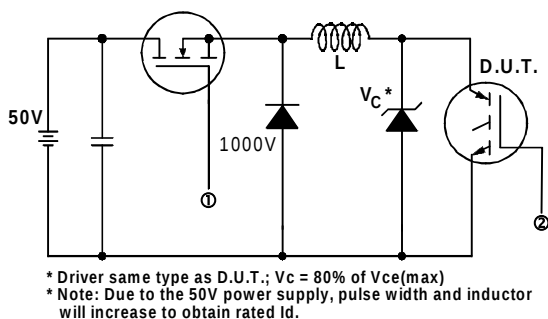


Fig. 13a - Clamped Inductive Load Test Circuit

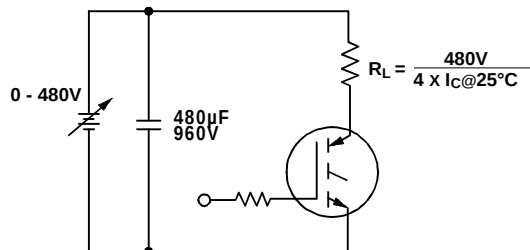


Fig. 13b - Pulsed Collector Current Test Circuit

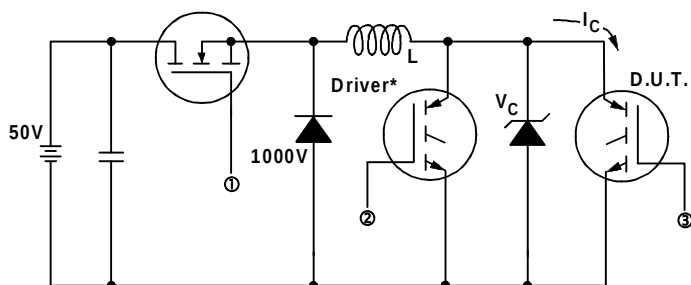


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = 480\text{V}$

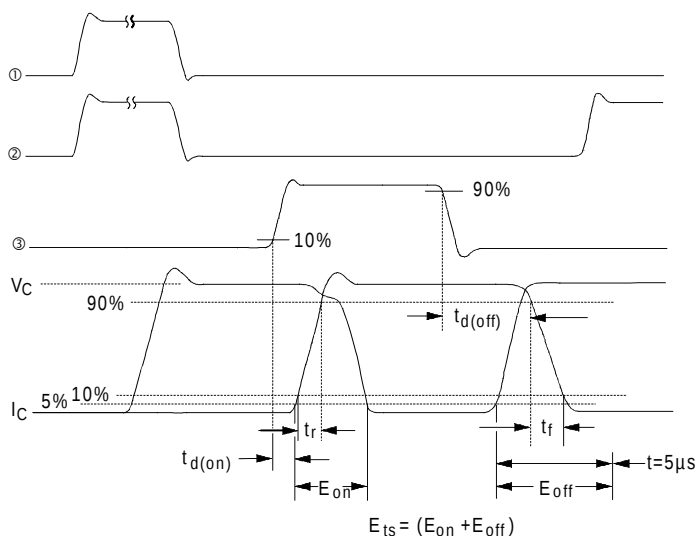
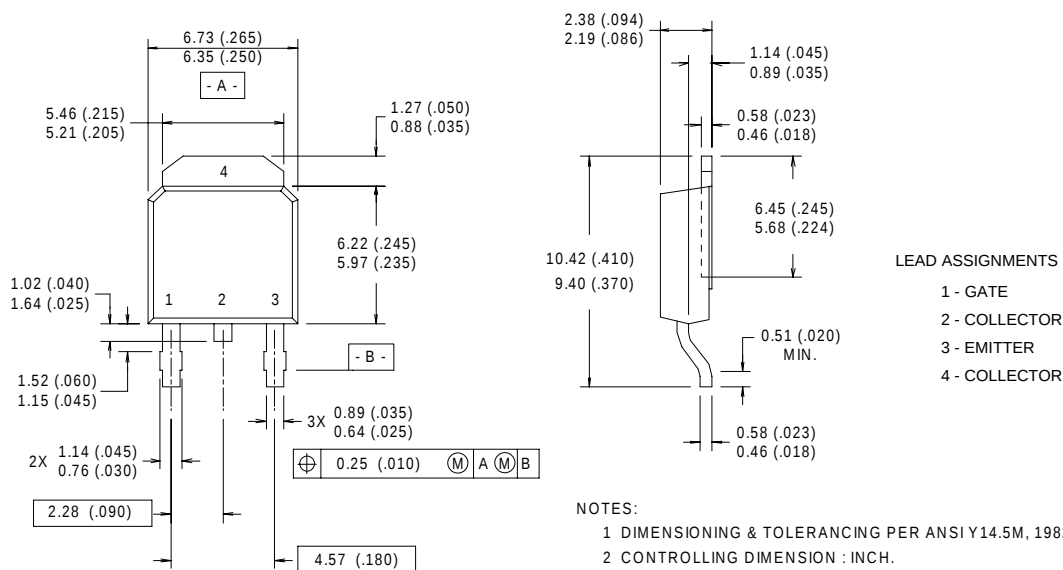


Fig. 14b - Switching Loss Waveforms

Package Outline

TO-252AA Outline

Dimensions are shown in millimeters (inches)



NOTES:

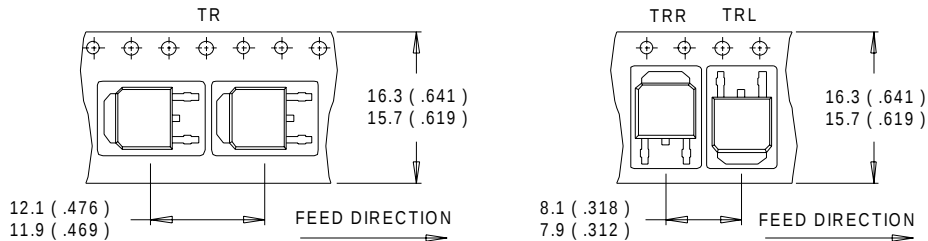
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH.
- 3 CONFORMS TO JEDEC OUTLINE TO-252AA.
- 4 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP,
SOLDER DIP MAX. +0.16 (.006).

IRG4RC10K

International
IR Rectifier

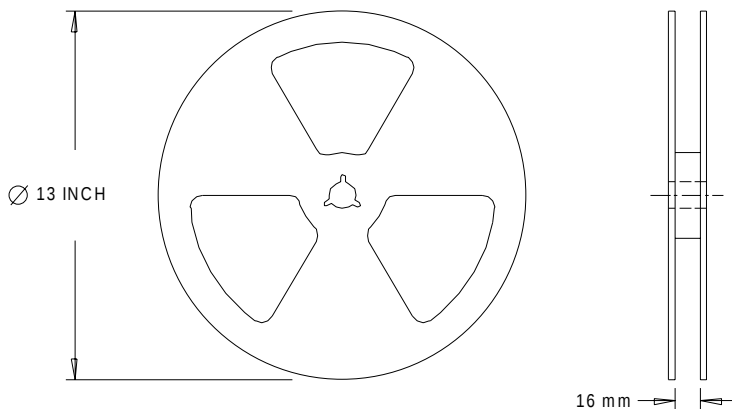
Tape & Reel Information

TO-252AA



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

International
IR Rectifier

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EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

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